

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
30V	460m Ω @ $V_{GS} = 4.5V$	1.1A
	560m Ω @ $V_{GS} = 2.5V$	1.0A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Backlighting
- DC-DC converters
- Power-management functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN3732UVTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

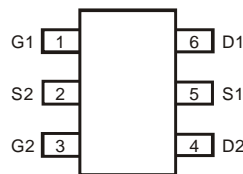
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

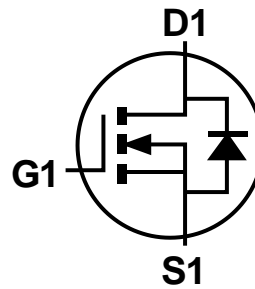
- Package: TSOT26
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.013 grams (Approximate)



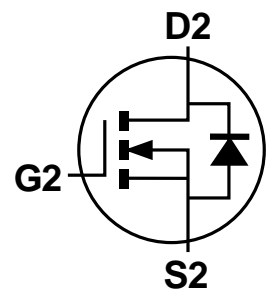
Top View



Top View



Q1 N-Channel

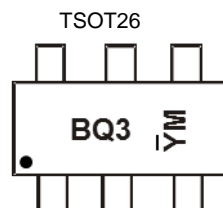


Q2 N-Channel

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN3732UVTQ-7	TSOT26	3,000	Tape & Reel
DMN3732UVTQ-13	TSOT26	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


BQ3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: K = 2023)
 M = Month (ex: 9 = September)

Date Code Key

Year	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	K	L	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings – N-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Q1 Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	I _D	1.1	A
Steady State		0.9	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	0.72	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	2.4	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.5	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	252	°C/W
Power Dissipation (Note 6)	P _D	0.8	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	150	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics – N-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.45	—	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	310	460	mΩ	V _{GS} = 4.5V, I _D = 200mA
			360	560		V _{GS} = 2.5V, I _D = 100mA
			430	730		V _{GS} = 1.8V, I _D = 75mA
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	40.8	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	7.6	—		
Reverse Transfer Capacitance	C _{rss}	—	4.6	—		
Total Gate Charge (V _{GS} = 10V)	Q _g	—	0.9	—		
Gate-Source Charge	Q _{gs}	—	0.05	—		
Gate-Drain Charge	Q _{gd}	—	0.3	—		
Turn-On Delay Time	t _{D(ON)}	—	1.1	—	ns	V _{DS} = 10V, I _D = 1A V _{GS} = 10V, R _g = 6Ω
Turn-On Rise Time	t _R	—	15.9	—		
Turn-Off Delay Time	t _{D(OFF)}	—	20.7	—		
Turn-Off Fall Time	t _F	—	20.0	—		

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

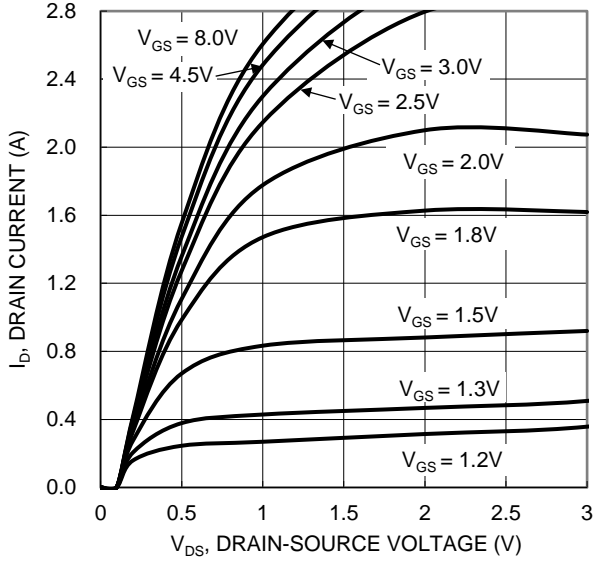


Figure 1. Typical Output Characteristic

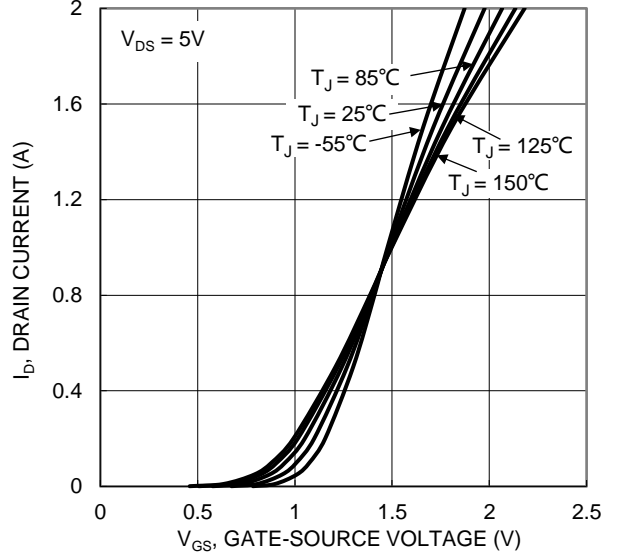


Figure 2. Typical Transfer Characteristic

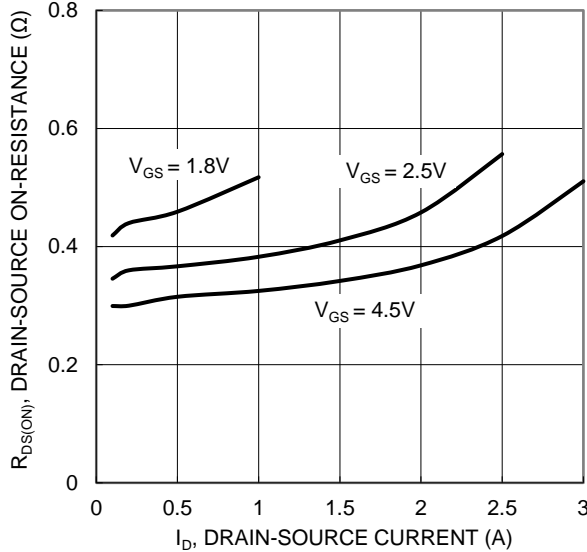


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

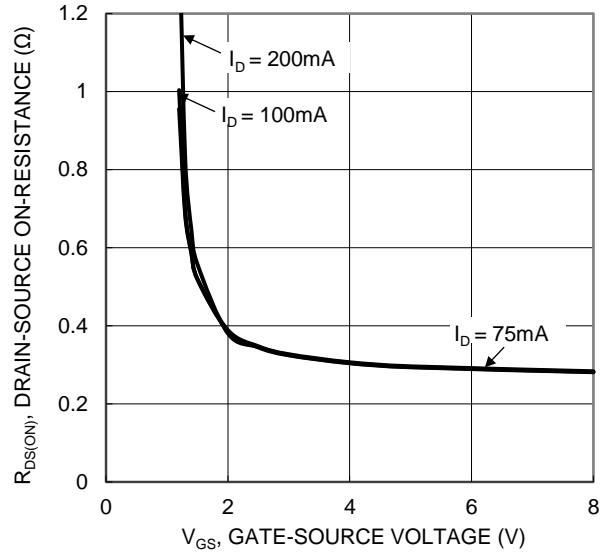


Figure 4. Typical Transfer Characteristic

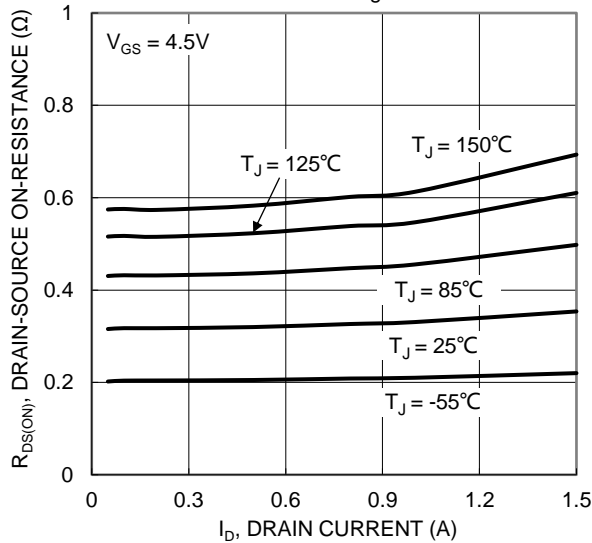


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

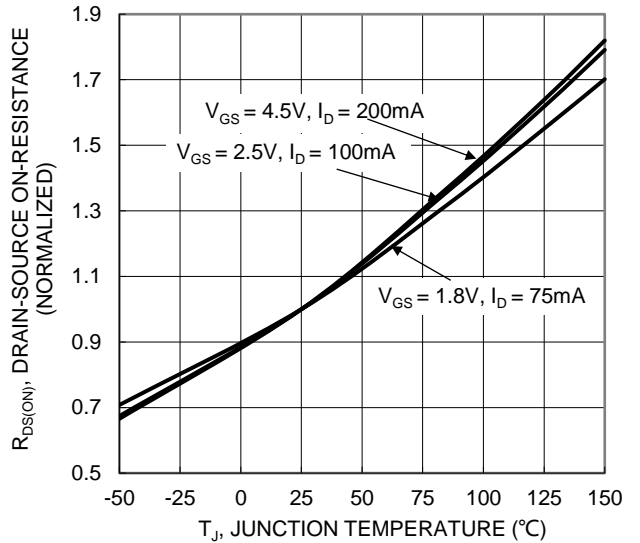


Figure 6. On-Resistance Variation with Junction Temperature

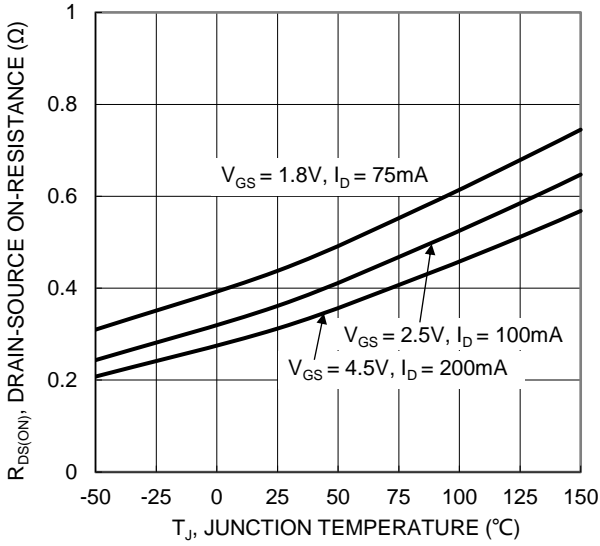


Figure 7. On-Resistance Variation with Junction Temperature

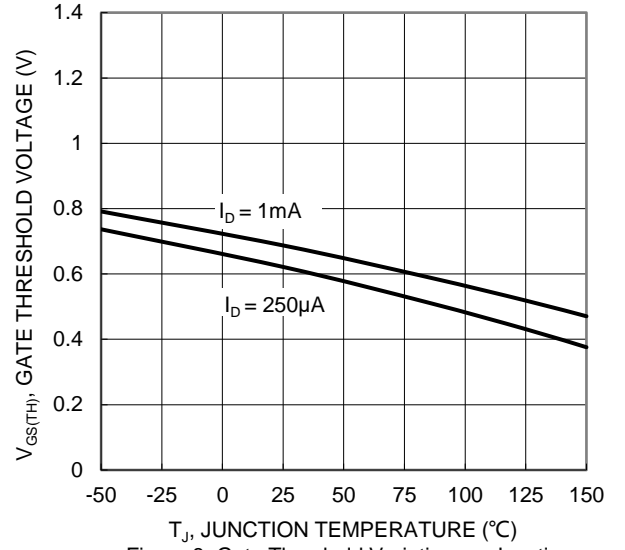


Figure 8. Gate Threshold Variation vs. Junction Temperature

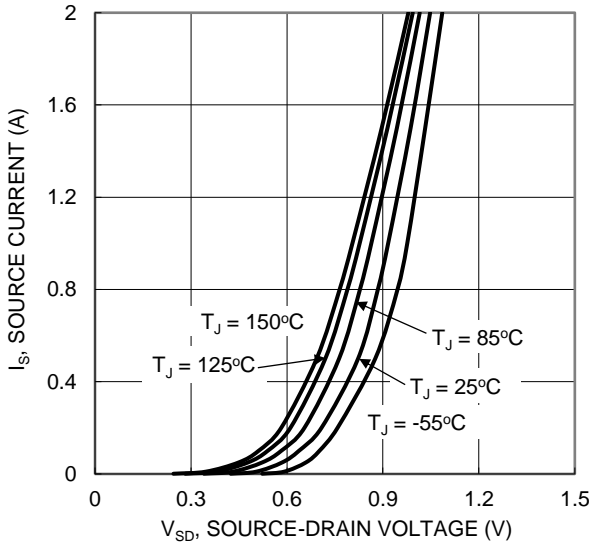


Figure 9. Diode Forward Voltage vs. Current

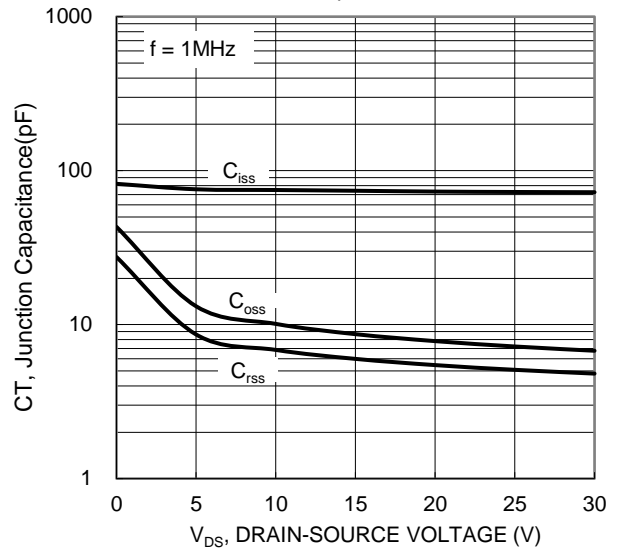


Figure 10. Typical Junction Capacitance

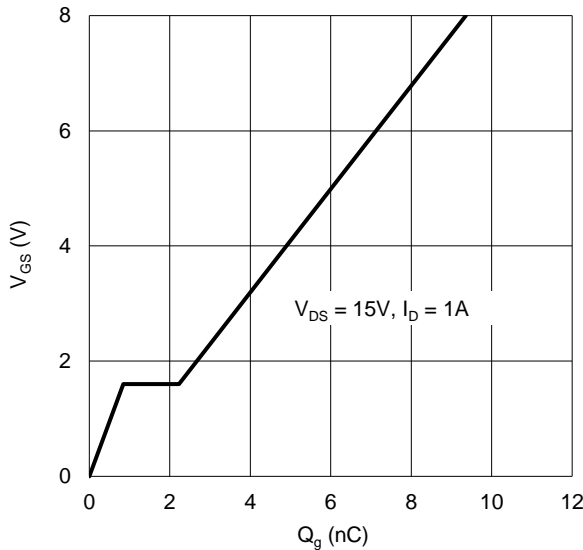


Figure 11. Gate Charge

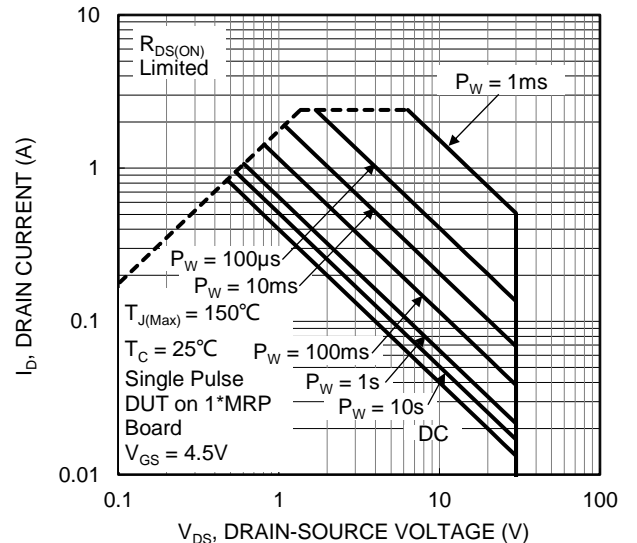


Figure 12. SOA, Safe Operation Area

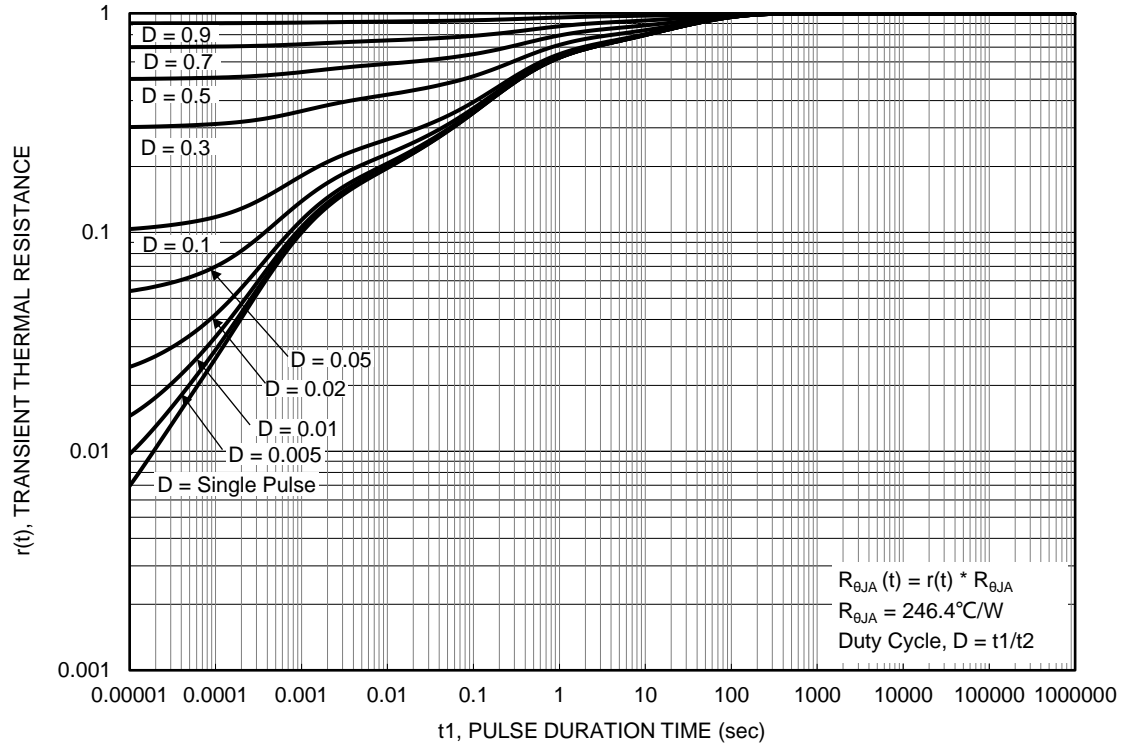
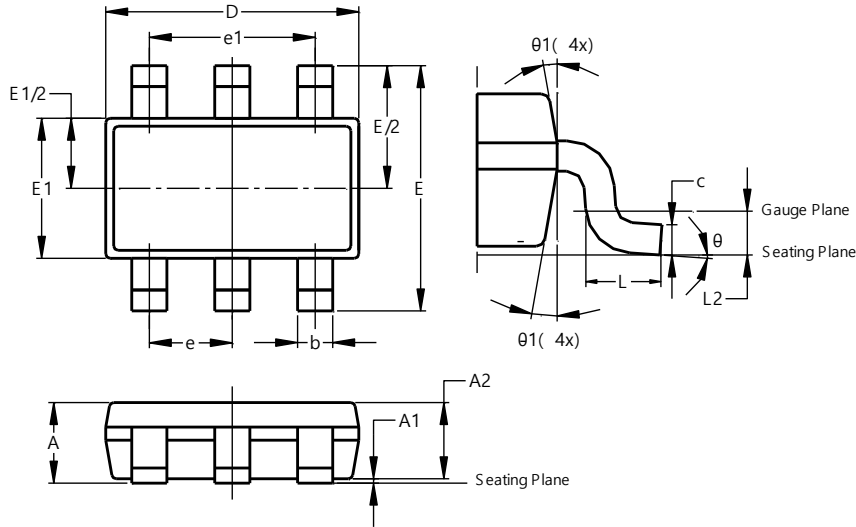


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

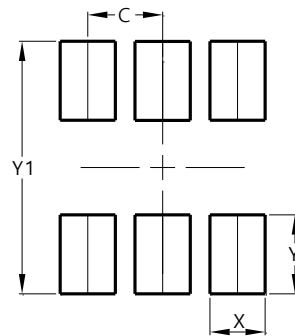


TSOT26			
Dim	Min	Max	Typ
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.200

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